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Team Nexperia



# PBSS5230T

# 30 V, 2 A PNP low VCEsat (BISS) transistor Rev. 2 — 4 June 2012

**Product data sheet** 

#### **Product profile** 1.

## 1.1 General description

PNP low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a SOT23 small Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4230T.

#### 1.2 Features and benefits

- Low collector-emiter saturation voltage
- High collector current capability: I<sub>C</sub> and I<sub>CM</sub>
- Higher efficiency leading to less heat generation
- AEC-Q101 qualified

## 1.3 Applications

- DC-to-DC conversion
- Supply line switching
- Battery charger
- LCD backlighting

- Driver in low supply voltage applications (e.g. lamps and LEDs)
- Inductive load driver (e.g. relays, buzzers and motors)

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-30	V
I <sub>C</sub>	collector current		-	-	-2	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	-3	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C}$ = -500 mA; $I_{B}$ = -50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	160	220	Ω



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# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		
2	Е	emitter	_ 3	3 
3	С	collector	1 2	1——
			SOT23 (TO-236AB)	2 sym013

# 3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS5230T	TO-236AB	plastic surface-mounted package; 3 leads	SOT23		

## 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
PBSS5230T	%3G

<sup>[1] % =</sup> placeholder for manufacturing site code

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	-30	V
$V_{CEO}$	collector-emitter voltage	open base		-	-30	V
$V_{EBO}$	emitter-base voltage	open collector		-	<b>-</b> 5	V
I <sub>C</sub>	collector current			-	-2	Α
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1$ ms		-	-3	Α
$I_{B}$	base current			-	-300	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	<u>[1]</u>	-	300	mW
			[2]	-	480	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
$T_{stg}$	storage temperature			-65	150	°C

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

PBSS5230

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<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

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## 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance	in free air	<u>[1]</u>	-	-	417	K/W
	from junction to ambient		[2]	-	-	260	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

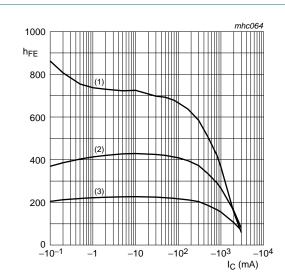
## 7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$I_{CBO}$	collector-base cut-off	$V_{CB}$ = -30 V; $I_E$ = 0 A; $T_{amb}$ = 25 °C	-	-	-100	nΑ
	current	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}; T_j = 150 \text{ °C}$	-	-	-50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -4 \text{ V; } I_{C} = 0 \text{ A; } T_{amb} = 25 ^{\circ}\text{C}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -2 V; $I_{C}$ = -100 mA; $T_{amb}$ = 25 °C	300	450	-	
		$V_{CE} = -2 \text{ V; } I_{C} = -1 \text{ A; pulsed;}$ $t_{p} \le 300 \text{ µs; } \delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	200	290	-	
		$V_{CE} = -2 \text{ V; } I_{C} = -2 \text{ A; pulsed;}$ $t_{p} \le 300 \text{ µs; } \delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	100	180	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}; T_{amb} = 25 \text{ °C}$	-	-70	-110	mV
		$I_C = -1 \text{ A}$ ; $I_B = -50 \text{ mA}$ ; $T_{amb} = 25 \text{ °C}$	-	-140	-225	mV
		$I_C = -2 \text{ A}$ ; $I_B = -200 \text{ mA}$ ; $T_{amb} = 25 \text{ °C}$	-	-240	-350	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -500 mA; $I_B$ = -50 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb} = 25 \ ^{\circ}C$	-	160	220	Ω
$V_{BEsat}$	base-emitter saturation voltage	$I_{C}$ = -2 A; $I_{B}$ = -50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 ; T_{amb} = 25 \ ^{\circ}C$	-	-	-1.1	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE}$ = -2 V; $I_{C}$ = -100 mA; $T_{amb}$ = 25 °C	-	-	-0.75	V
f <sub>T</sub>	transition frequency	$V_{CE} = -10 \text{ V}; I_{C} = -100 \text{ mA};$ f = 100 MHz; $T_{amb} = 25 \text{ °C}$	100	200	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$	-	23	28	pF

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

#### 30 V, 2 A PNP low VCEsat (BISS) transistor



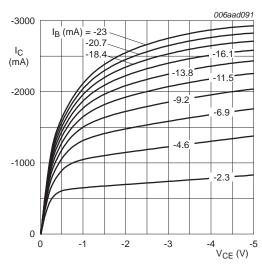
$$V_{CE} = -2 V$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

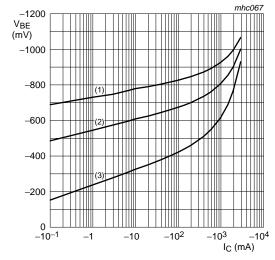
(3) 
$$T_{amb} = -55$$
 °C

Fig 1. DC current gain as a function of collector current; typical values



T<sub>amb</sub> = 25 °C

Fig 2. Collector current as a function of collector-emitter voltage; typical values



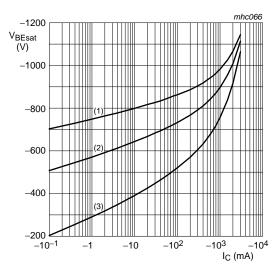
$$V_{CE} = -2 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 3. Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

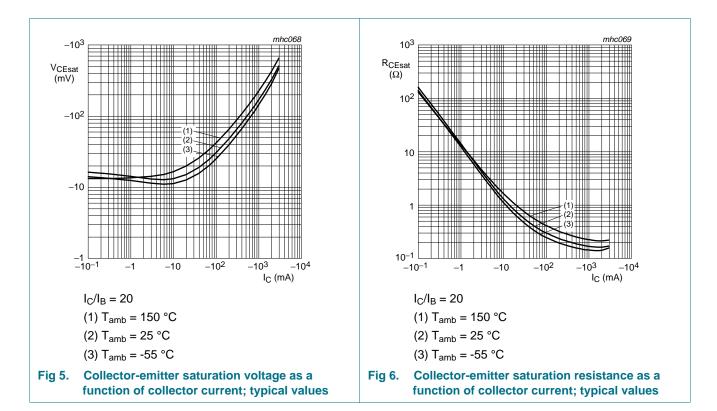
(1) 
$$T_{amb} = -55$$
 °C

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 4. Base-emitter saturation voltage as a function of collector current; typical values

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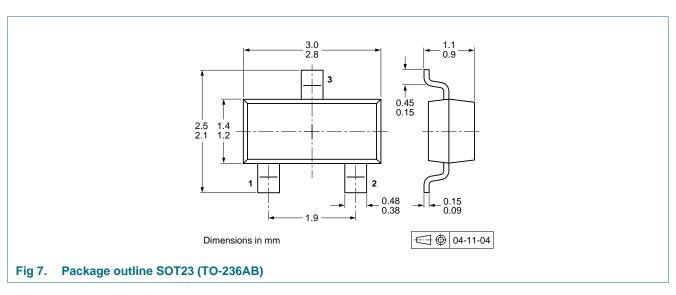


## 8. Test information

#### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

## 9. Package outline



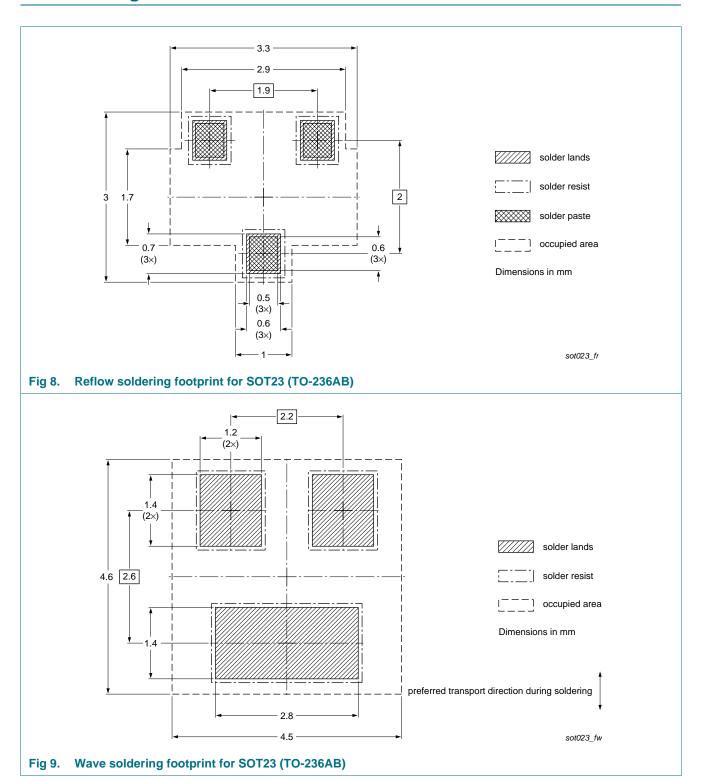
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#### 30 V, 2 A PNP low VCEsat (BISS) transistor

# 10. Soldering



# 30 V, 2 A PNP low VCEsat (BISS) transistor

# 11. Revision history

#### Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
PBSS5230T v.2	20120604	Product data sheet	-	PBSS5230T v.1	
Modifications:	<ul> <li>The format of this document has been redesigned to comply with the new identity NXP Semiconductors.</li> </ul>				
	<ul> <li>Legal texts have</li> </ul>	e been adapted to the new	company name where	appropriate.	
<ul> <li>1 "Product profile": updated</li> </ul>					
<ul> <li>4 "Marking": corrected</li> </ul>					
	• <u>Table 5.</u> : upda	ted			
	<ul> <li><u>7 "Characteristics"</u>: V<sub>CEsat</sub> corrected, <u>Fig 1.</u> to <u>Fig 6.</u> added</li> </ul>				
	• 8 "Test information": added				
<ul> <li>9 "Package outline": replaced by minimized package outline drawing</li> </ul>				ving	
	• 10 "Soldering"	: added			
PBSS5230T v.1	20031218	Product data sheet	-	-	

#### 30 V, 2 A PNP low VCEsat (BISS) transistor

## 12. Legal information

#### 12.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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# 30 V, 2 A PNP low VCEsat (BISS) transistor

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